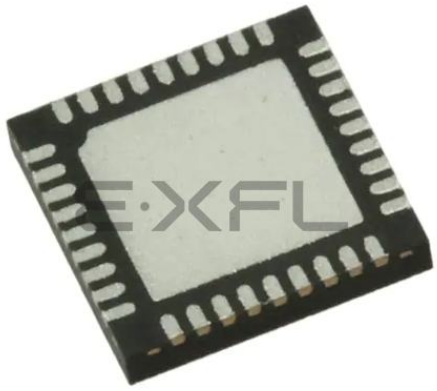

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	26
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	36-VFQFN Exposed Pad
Supplier Device Package	36-VFQFPN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f101t6u6

2.2 Full compatibility throughout the family

The STM32F101xx is a complete family whose members are fully pin-to-pin, software and feature compatible. In the reference manual, the STM32F101x4 and STM32F101x6 are referred to as low-density devices, the STM32F101x8 and STM32F101xB are referred to as medium-density devices, and the STM32F101xC, STM32F101xD and STM32F101xE are referred to as high-density devices.

Low- and high-density devices are an extension of the STM32F101x8/B devices, they are specified in the STM32F101x4/6 and STM32F101xC/D/E datasheets, respectively. Low-density devices feature lower Flash memory and RAM capacities and a timer less. High-density devices have higher Flash memory and RAM capacities, and additional peripherals like FSMC and DAC, while remaining fully compatible with the other members of the STM32F101xx family.
The STM32F101x4, STM32F101x6, STM32F101xC, STM32F101xD and STM32F101xE are a drop-in replacement for the STM32F101x8/B medium-density devices, allowing the user to try different memory densities and providing a greater degree of freedom during the development cycle.

Moreover, the STM32F101xx performance line family is fully compatible with all existing STM32F101xx access line and STM32F102xx USB access line devices.

Table 3. STM32F101xx family

	Memory size						
	Low-density devices		Medium-density devices		High-density devices		
Pinout	16 KB Flash	32 KB Flash(1)	64 KB Flash	128 KB Flash	256 KB Flash	384 KB Flash	512 KB Flash
	4 KB RAM	6 KB RAM	10 KB RAM	16 KB RAM	32 KB RAM	48 KB RAM	48 KB RAM
144	-	-	-	-	5 × USARTs 4 × 16-bit timers, 2 × basic timers 3 × SPIs, 2 × I^2		

1. For orderable part numbers that do not show the A internal code after the temperature range code (6), the reference datasheet for electrical characteristics is that of the STM32F101x8/B medium-density devices.

Table 4. Low-density STM32F101xx pin definitions

Pins			Pin name	Type(1)	I / O level(2)	Main function(3) (after reset)	Alternate functions(3)(4)	
LQFP48	LQFP64	VFQFPN36					Default	Remap
1	1	-	V_{BAT}	S	-	V_{BAT}	-	-
2	2	-	PC13-TAMPER-RTC(5)	I/O	-	PC13(6)	TAMPER-RTC	-
3	3	-	PC14-OSC32_IN(5)	I/O	-	PC14(6)	OSC32_IN	-
4	4	-	PC15-OSC32_OUT(5)	I/O	-	PC15(6)	OSC32_OUT	-
5	5	2	OSC_IN	I	-	OSC_IN	-	-
6	6	3	OSC_OUT	O	-	OSC_OUT	-	-
7	7	4	NRST	I/O	-	NRST	-	-
-	8	-	PC0	I/O	-	PC0	ADC_IN10	-
-	9	-	PC1	I/O	-	PC1	ADC_IN11	-
-	10	-	PC2	I/O	-	PC2	ADC_IN12	-
-	11	-	PC3	I/O	-	PC3	ADC_IN13	-
8	12	5	V_{SSA}	S	-	V_{SSA}	-	-
9	13	6	V_{DDA}	S	-	V_{DDA}	-	-
10	14	7	PA0-WKUP	I/O	-	PA0	WKUP/USART2_CTS/ ADC_IN0/ TIM2_CH1_ETR(7)	-
11	15	8	PA1	I/O	-	PA1	USART2_RTS/ ADC_IN1/TIM2_CH2(7)	-
12	16	9	PA2	I/O	-	PA2	USART2_TX/ ADC_IN2/TIM2_CH3(7)	-
13	17	10	PA3	I/O	-	PA3	USART2_RX/ ADC_IN3/TIM2_CH4(7)	-
-	18	-	V_{SS_4}	S	-	V_{SS_4}	-	-
-	19	-	V_{DD_4}	S	-	V_{DD_4}	-	-
14	20	11	PA4	I/O	-	PA4	SPI_NSS(7)/ADC_IN4 USART2_CK	-
15	21	12	PA5	I/O	-	PA5	SPI_SCK(7)/ADC_IN5	-
16	22	13	PA6	I/O	-	PA6	SPI_MISO(7)/ADC_IN6/ TIM3_CH1(7)	-

Table 6. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD}/V_{DDA} power lines (source)(1)	150	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink)(1)	150	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current source by any I/Os and control pin	–25	
$I_{INJ(PIN)}$(2)	Injected current on five volt tolerant pins(3)	-5/+0	
	Injected current on any other pin(4)	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(5)	± 25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. Negative injection disturbs the analog performance of the device. See note in *Section 5.3.17: 12-bit ADC characteristics*.
3. Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 5: Voltage characteristics* for the maximum allowed input voltage values.
4. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 5: Voltage characteristics* for the maximum allowed input voltage values.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 7. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

5.3 Operating conditions

5.3.1 General operating conditions

Table 8. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	36	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	36	
f_{PCLK2}	Internal APB2 clock frequency	-	0	36	
V_{DD}	Standard operating voltage	-	2	3.6	V
V_{DDA}(1)	Analog operating voltage (ADC not used)	Must be the same potential as V_{DD}(2)	2	3.6	
	Analog operating voltage (ADC used)		2.4	3.6	
V_{BAT}	Backup operating voltage	-	1.8	3.6	

Table 14. Maximum current consumption in Sleep mode, code running from Flash or RAM

Symbol	Parameter	Conditions	f_{HCLK}	Max(1)	Unit
				T_A = 85 °C	
I_{DD}	Supply current in Sleep mode	External clock(2) all peripherals enabled	36 MHz	14	mA
			24 MHz	10	
			16 MHz	7	
			8 MHz	4	
		External clock(2), all peripherals disabled	36 MHz	5	
			24 MHz	4.5	
			16 MHz	4	
			8 MHz	3	

1. Based on characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
2. External clock is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 15. Typical and maximum current consumptions in Stop and Standby modes

Symbol	Parameter	Conditions	Typ(1)			Max	Unit
			V_{DD}/V_{BAT} = 2.0 V	V_{DD}/V_{BAT} = 2.4 V	V_{DD}/V_{BAT} = 3.3 V	T_A = 85 °C(2)	
I_{DD}	Supply current in Stop mode	Regulator in Run mode, Low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	21.3	21.7	160	µA
		Regulator in Low Power mode, Low-speed and high-speed internal RC oscillators and high-speed oscillator OFF (no independent watchdog)	-	11.3	11.7	145	
	Supply current in Standby mode	Low-speed internal RC oscillator and independent watchdog ON	-	2.6	3.4	-	
		Low-speed internal RC oscillator ON, independent watchdog OFF	-	2.4	3.2	-	
		Low-speed internal RC oscillator and independent watchdog OFF, low-speed oscillator and RTC OFF	-	1.7	2	3.2	
I_{DD_VBAT}	Backup domain supply current	Low-speed oscillator and RTC ON	0.9	1.1	1.4	1.9	

1. Typical values are measured at T_A = 25 °C.
2. Based on characterization, not rested in production.

Table 18. Peripheral current consumption

	Peripheral	Typical consumption at 25 °C	Unit
AHB (up to 36 MHz)	DMA1	15.97	A/MHz
	CRC	1.67	
	BusMatrix(1)	8.33	
APB1 (up to 18 MHz)	APB1-Bridge	7.22	
	TIM2	33.33	
	TIM3	33.61	
	USART2	12.78	
	I2C1	10.83	
	WWDG	3.33	
	PWR	1.94	
	BKP	2.78	
	IWDG	1.39	
APB2 (up to 36 MHz)	APB2-Bridge	3.33	
	GPIO A	7.50	
	GPIO B	6.81	
	GPIO C	7.22	
	GPIO D	6.94	
	SPI1	4.86	
	USART1	12.78	
	ADC1(2)		

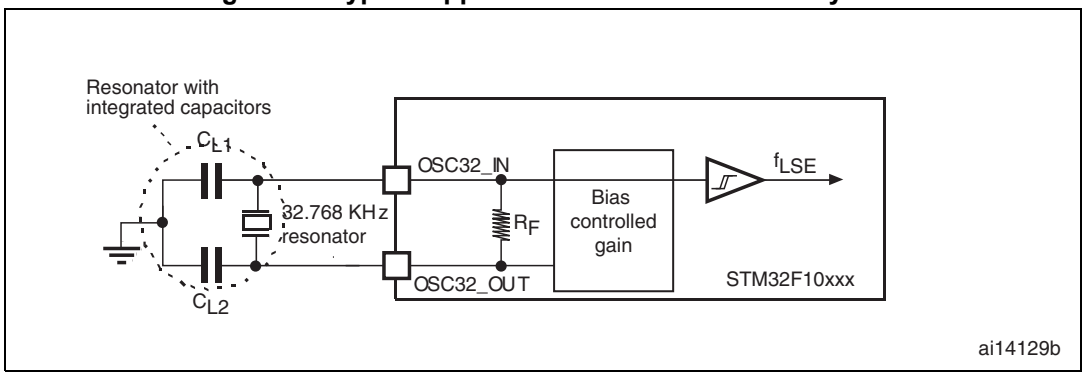
1. The BusMatrix is automatically active when at least one master is ON. (CPU, DMA1).
2. Specific conditions for measuring ADC current consumption: f_{HCLK} = 28 MHz, $f_{APB1} = f_{HCLK}$, $f_{APB2} = f_{HCLK}$, $f_{ADCCLK} = f_{APB2} / 2$. When ADON bit in the ADC_CR2 register is set to 1, a current consumption of analog

5.3.6 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in Table 19 result from tests performed using an high-speed external clock source, and under the ambient temperature and supply voltage conditions summarized in Table 8.

Figure 21. Typical application with a 32.768 kHz crystal



5.3.7 Internal clock source characteristics

The parameters given in *Table 23* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 8*.

High-speed internal (HSI) RC oscillator

Table 23. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
f_{HSI}	Frequency	-		-	8	-	MHz
$DuCy_{(HSI)}$	Duty cycle	-		45	-	55	%
ACC_{HSI}	Accuracy of the HSI oscillator	User-trimmed with the RCC_CR register(2)		-	-	1(3)	%
		Factory-calibrated (4) (5)	T_A = –40 to 105 °C	–2	-	2.5	%
			T_A = –10 to 85 °C	–1.5	-	2.2	%
			T_A = 0 to 70 °C	–1.3	-	2	%
			T_A = 25 °C	–1.1	-	1.8	%
$t_{su(HSI)}$(4)	HSI oscillator startup time	-		1	-	2	µs
$I_{DD(HSI)}$(4)	HSI oscillator power consumption	-		-	80	100	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Refer to application note AN2868 “STM32F10xxx internal RC oscillator (HSI) calibration” available from the ST website *www.st.com*.
3. Guaranteed by design, not tested in production.
4. Based on characterization, not tested in production.
5. The actual frequency of HSI oscillator may be impacted by a reflow, but does not drift out of the specified range.

5.3.11 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78 IC latch-up standard.

5.3.12 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibilty to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

Figure 24. 5 V tolerant I/O input characteristics - CMOS port

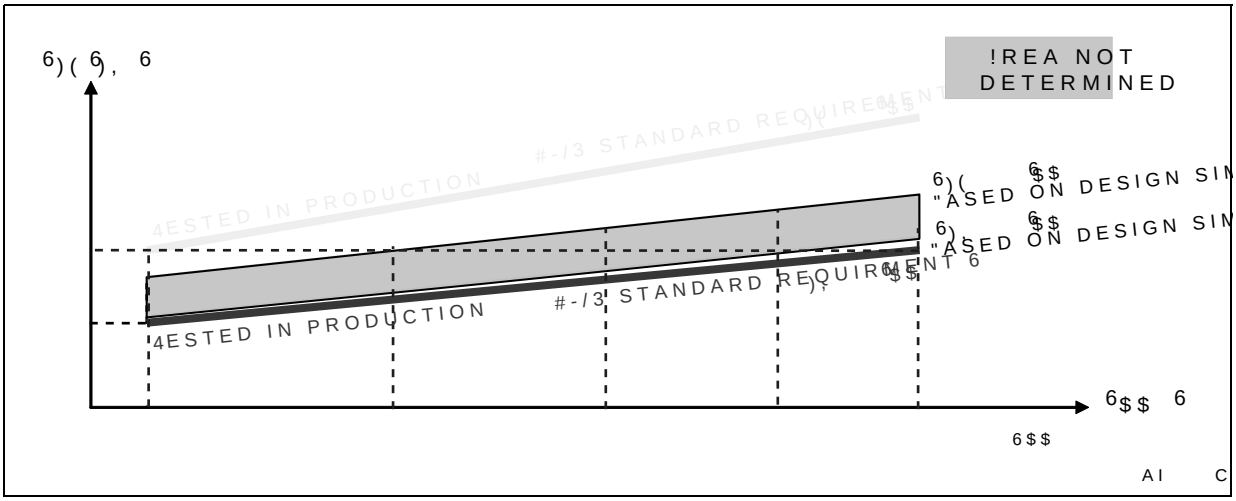


Figure 25. 5 V tolerant I/O input characteristics - TTL port

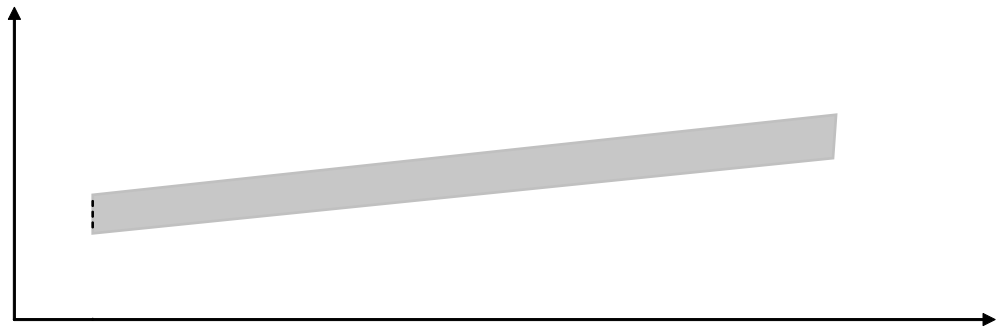


Figure 29. SPI timing diagram - slave mode and CPHA = 0

Figure 30. SPI timing diagram - slave mode and CPHA = 1(1)

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.